P-Ch 30V Fast Switching MOSFETs

★ 100% EAS Guaranteed
★ Green Device Available
★ Super Low Gate Charge
★ Excellent CdV/dt effect decline
★ Advanced high cell density Trench technology

Product Summary

Green

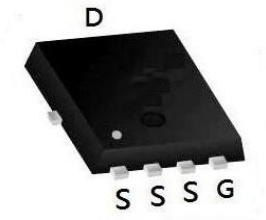
BVDSS	RDSON	ID
-30V	7.5mΩ	-55A

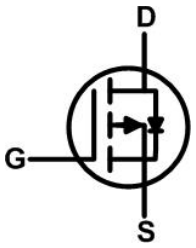
Description

The XR60P03D is the highest performance trench P-ch MOSFETs with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The XR60P03D meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

PDFN3333-8L Pin Configuration





Absolute Maximum Ratings (T_A = 25°C, unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_C=25°C	I_D	-55	A
	T_C=100°C		-30	
Pulsed Drain Current[1]		I_{DM}	-168	A
Single Pulse Avalanche Energy[2]		EAS	45	mJ
Total Power Dissipation	T_C=25°C	P_D	37	W
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction-to-Ambient[3]	$R_{\theta JA}$	75	°C/W
Thermal Resistance from Junction-to-Case	$R_{\theta JC}$	3.36	°C/W

Electrical Characteristics (T_J = 25°C, unless otherwise noted)

Parameter		Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics							
Drain-Source Breakdown Voltage		$V_{(BR)DSS}$	V_{GS} = 0V, I_D = -250μA	-30	-	-	V
Gate-body Leakage current		I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V	-	-	±100	nA
Zero Gate Voltage Drain Current	T_J=25℃	I_{DSS}	V_{DS} = -30V, V_{GS} = 0V	-	-	-1	μA
	T_J=100℃			-	-	-100	
Gate-Threshold Voltage		$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250μA	-1.0	-	-2.5	V
Drain-Source On-Resistance[4]		$R_{DS(on)}$	V_{GS} = -10V, I_D = -30A	-	7.5	14	mΩ
			V_{GS} = -4.5V, I_D = -15A	-	10	22	
Forward Transconductance[4]		g_{fs}	V_{DS} = -5V, I_D = -30A	-	57	-	S
Dynamic Characteristics[5]							
Input Capacitance		C_{iss}	V_{DS} = -15V, V_{GS} =0V, f =1MHz	-	2396	-	pF
Output Capacitance		C_{oss}		-	325	-	
Reverse Transfer Capacitance		C_{rss}		-	283	-	
Gate Resistance		R_g	f =1MHz	-	10.5	-	Ω
Switching Characteristics[5]							
Total Gate Charge		Q_g	V_{GS} = -10V,V_{DS} = -15V, I_D= -30A	-	30	-	nC
Gate-Source Charge		Q_{gs}		-	5	-	
Gate-Drain Charge		Q_{gd}		-	7.5	-	
Turn-On Delay Time		$t_{d(on)}$	V_{GS} = -10V, V_{DD} = -15V, R_G = 3Ω, I_D= -30A	-	14.1	-	ns
Rise Time		t_r		-	20	-	
Turn-Off Delay Time		$t_{d(off)}$		-	94	-	
Fall Time		t_f		-	65	-	
Body Diode Reverse Recovery Time		t_{rr}	I_F = -30A, dI/dt = 100A/μs	-	19	-	ns
Body Diode Reverse Recovery Charge		Q_{rr}		-	9	-	nC
Drain-Source Body Diode Characteristics							
Diode Forward Voltage[4]		V_{SD}	I_S = -1A, V_{GS} = 0V	-	-	-1.2	V
Continuous Source Current	T_C=25°C	I_S	-	-	-	-55	A

Note :

1. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150°C.
2. The EAS data shows Max. rating . The test condition is V_{DD}= -25V, V_{GS}= -10V, L= 0.1mH, I_{AS}= -30A.
3. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
4. The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.
5. This value is guaranteed by design hence it is not included in the production test.

Typical Characteristics

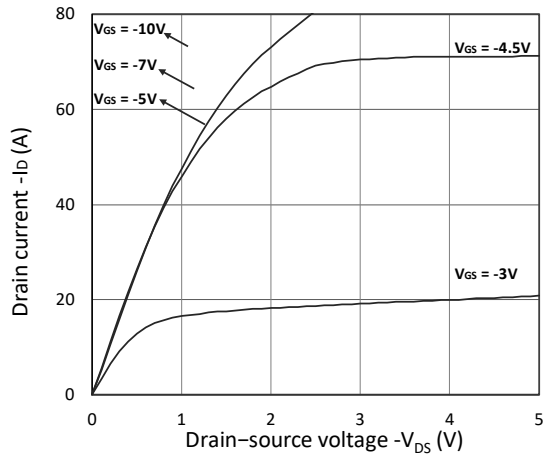


Figure 1. Output Characteristics

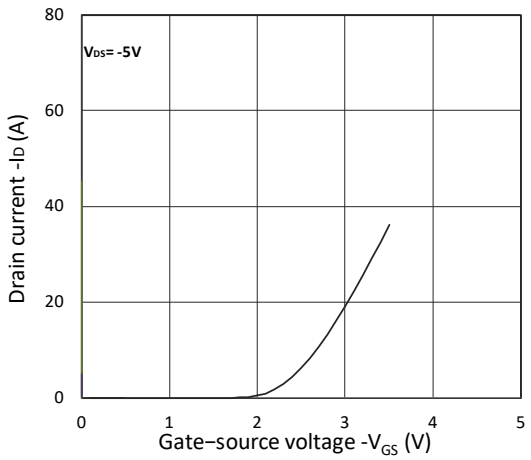


Figure 2. Transfer Characteristics

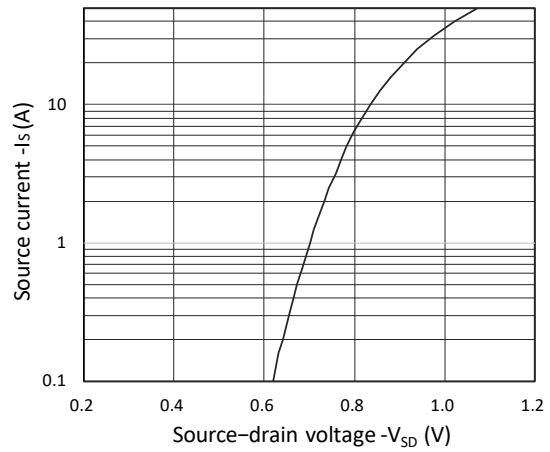


Figure 3. Forward Characteristics of Reverse

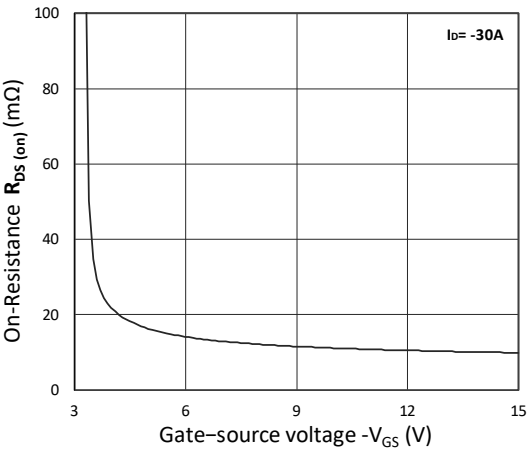


Figure 4. $R_{DS(ON)}$ vs. V_{GS}

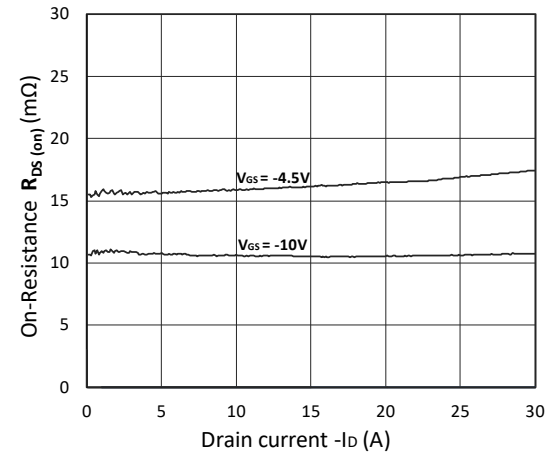


Figure 5. $R_{DS(ON)}$ vs. I_D

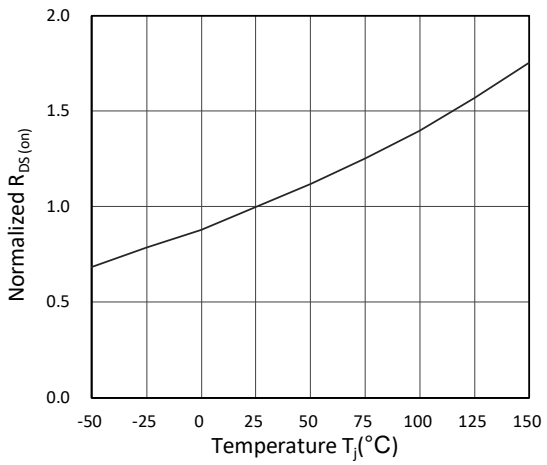


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

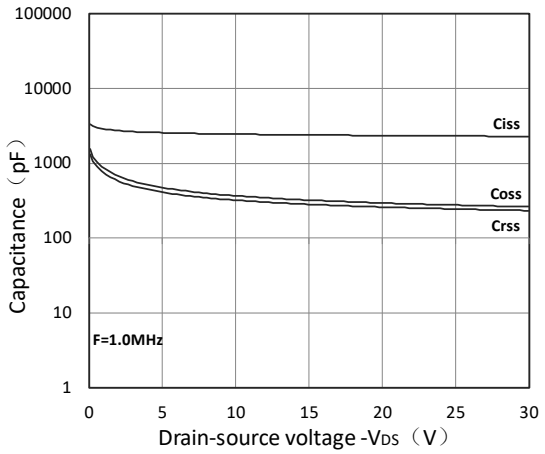


Figure 7. Capacitance Characteristics

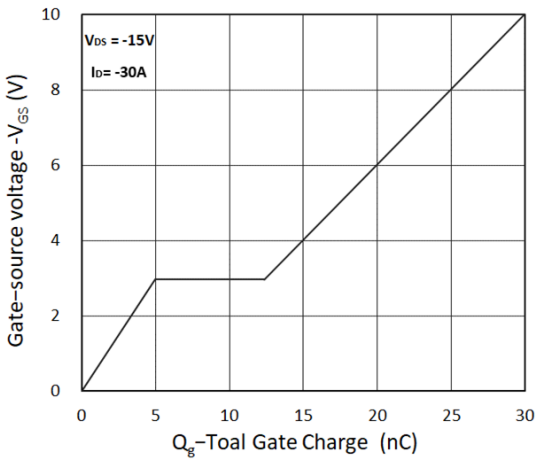


Figure 8. Gate Charge Characteristics

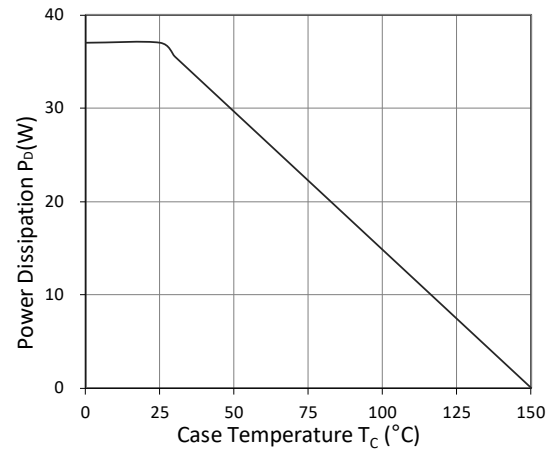


Figure 9. Power Dissipation

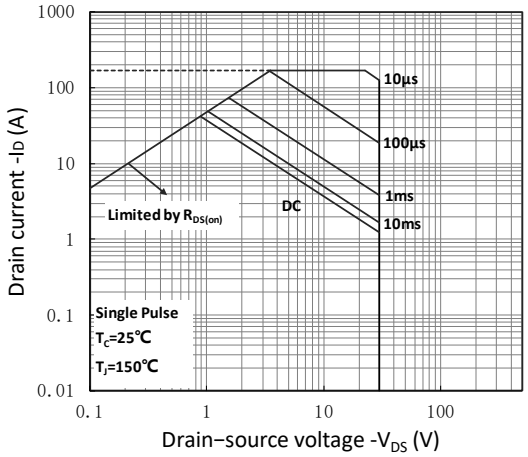


Figure10. Safe Operating Area

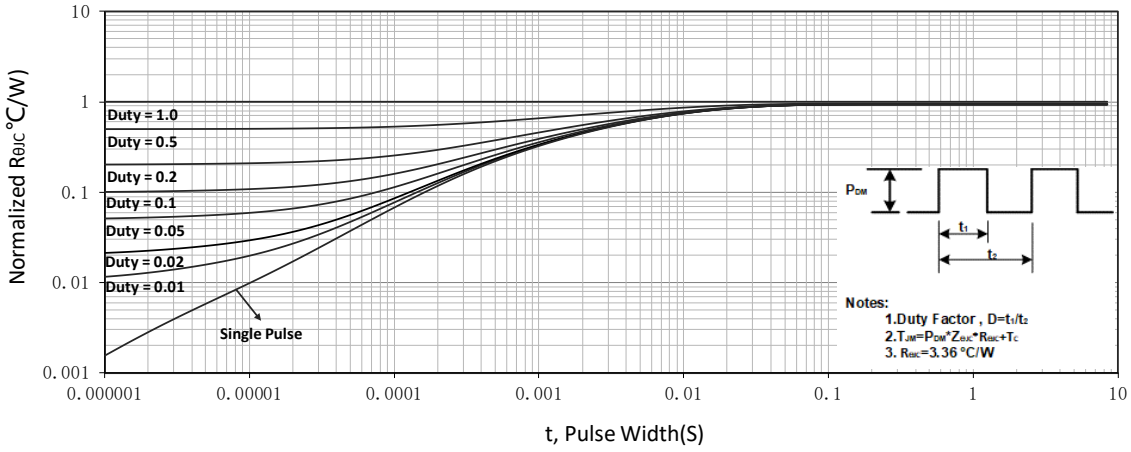
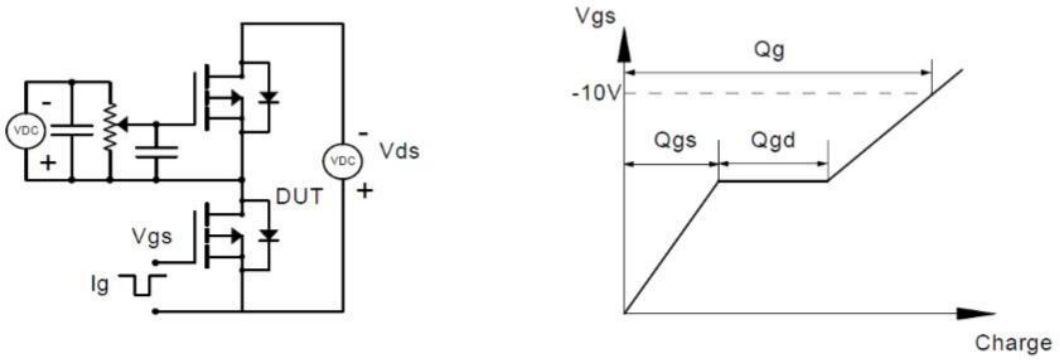


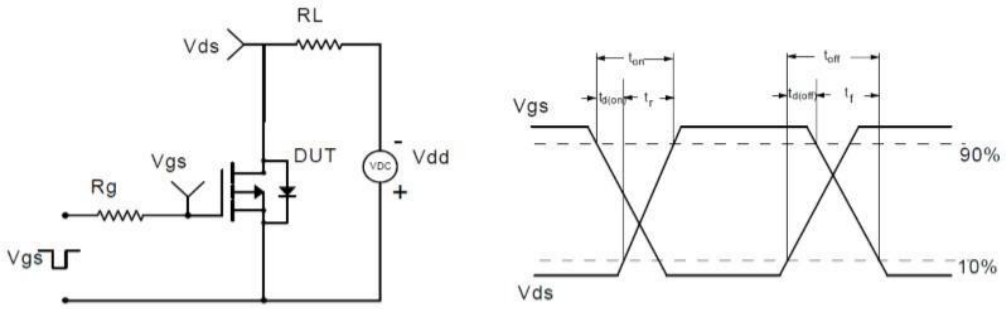
Figure 11. Normalized Maximum Transient Thermal Impedance

Test Circuit

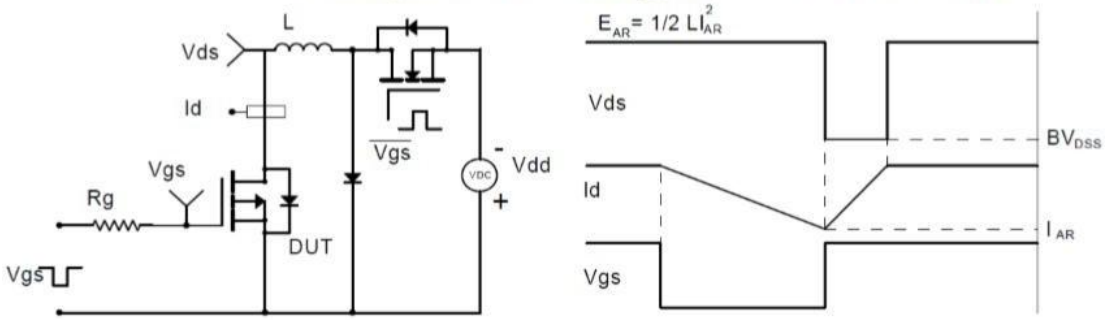
Gate Charge Test Circuit & Waveform



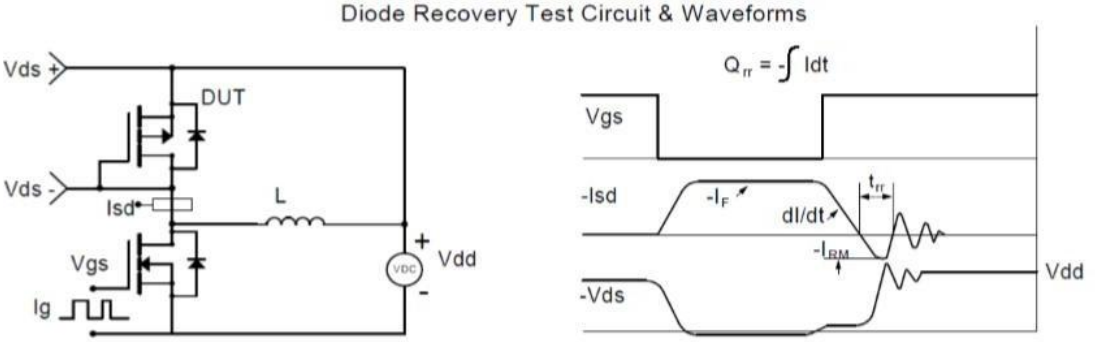
Resistive Switching Test Circuit & Waveforms



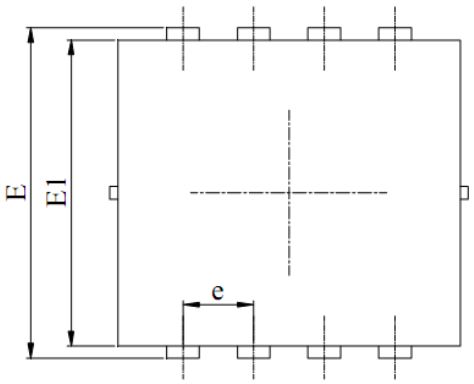
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



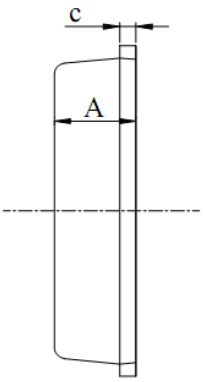
Diode Recovery Test Circuit & Waveforms



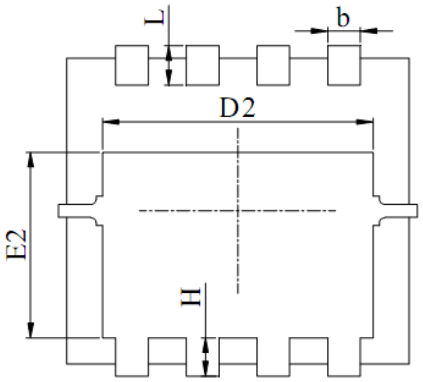
Package Mechanical Data-PDFN3333-8L-Single



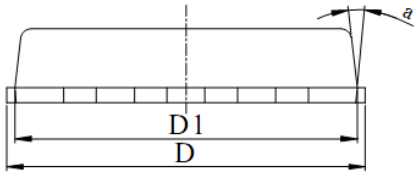
Top View



Side View



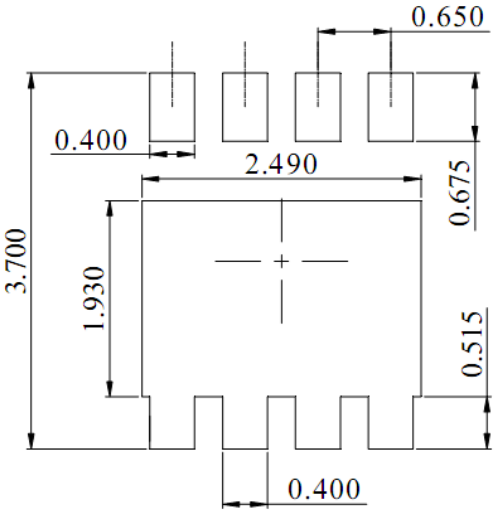
Bottom View



Front View

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
2. ALL DIMNESIONS IN MILLIMETER (ANNGLE IN DEGREE).
3. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.20	0.25
D	3.00	3.15	3.25
D1	2.95	3.05	3.15
D2	2.39	2.49	2.59
E	3.20	3.30	3.40
E1	2.95	3.05	3.15
E2	1.70	1.80	1.90
e	0.65 BSC		
H	0.30	0.40	0.50
L	0.25	0.40	0.50
a	---	---	15°



DIMENSIONS:MILLIMETERS